Load Pull Characteristics of GaAs MESFETs Calculated Using an Analytic, Physics Based Large Signal Device Model

D.E. Stoneking, R.J. Trew and J.B. Yan. "Load Pull Characteristics of GaAs MESFETs Calculated Using an Analytic, Physics Based Large Signal Device Model." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 1057-1060.

The large signal nonlinear load pull characteristics of power GaAs MESFETs fabricated with uniform, ion-implanted, and lo-hi-lo doping profiles are calculated theoretically and compared. The calculation is performed using a load pull simulator in conjunction with a new physics based, analytic device model. The device and circuit models are interfaced using a harmonic balance routine.

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